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The cost of remembering

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In 1961 Landauer pointed out that resetting a binary memory requires a minimum energy of $k_B T\ ln(2)$ where k_B is the Boltzmann constant and T the absolute temperature of the memory device. Any memory however, is doomed to loose its content as time proceeds if no action is taken. In order to avoid memory loss, a refresh procedure is periodically performed with time interval t_R. In this paper we show that it does exist a fundamental bound to the minimum energy required to preserve one bit of information for a time $\bar{t}$, with probability of error less than P_E, and that this energy is a monotonically decreasing function of t_R. Two main conclusions are drawn: the good news is that, in principle, the cost of remembering can be arbitrarily reduced if the refresh procedure is performed often enough. The bad news is that no memory can be preserved forever, no matter how much energy is invested.

Introduction

The act of remembering is of fundamental importance in human life. It involves any trace that humankind has left in his long history on this planet. Not only manmade objects, monuments and landscapes require maintenance to counterbalance the effect of time that levels out differences, but also biological systems are subjected to the never-ending task of preserving memories, i.e. shapes and functionalities, by fighting the universal tendency of entropy to increase. The study of fundamental physical limits in writing[1] and preserving memories has recently received considerable attention in different contests: communication-theoretic paradigms[2], biological noisy neural networks [3,4] and future technologies[5]. In this work we will focus on classical information stored in digital devices, however the main conclusions here are valid in the wider class of analogue memory preserving devices and in principle apply to any system that needs to maintain a given configuration.

By the moment that in digital devices the information is usually stored in the form of binary numbers, where the "0" bit is valued the same as the "1" bit, it is customary[1, 6, 7, 8] to use an abstract representation of such devices in terms of dynamic systems with two equally energetic stable states separated by a potential barrier (fig. 1a). The potential barrier separates the two logic states ($x<0$, representing bit "0" and $x>0$, representing bit "1") and confines the dynamics within one of the states, as required by the memorization process (fig. 1b). This is clearly a non-equilibrium condition that evolves, within the system relaxation time τ_K, to thermal equilibrium (fig. 1f). As this process takes place (fig. 1c to fig. 1f), memorization errors accumulate up to the point that the memorized bit is statistically lost when thermal equilibrium is achieved.

In order to fight information loss it is thus customary to set up a procedure that acts against the relaxation process in the memory device. In practical digital memories this is achieved through a cyclic refresh operation, consisting in a read-and-rewrite memory process executed at periodic interval of duration t_R. The read-and-rewrite memory operation takes a time t_p (protocol time) during which the memory is not

available. In modern computing systems t_p is few nanoseconds, t_R few milliseconds and τ_K few seconds[9]. This memory refreshing procedure, indeed, is not limited to information encoded in binary digits but it is in general common to any form of memory preservation, as for example in restoration operations in ancient masterpieces or in buildings maintenance, just with different values for t_p, t_R and τ_K. The relaxation to equilibrium process is a statistical one and, once the memory has been written, there is always a finite probability that within any given time $\bar{t}$ the system crosses the potential barrier and ends in the wrong logic state. If by chance the wrong bit is read, then the memory is overwritten with the wrong logic value. This occurs because the refresh operation does not correct errors. Thus any memory preservation strategy is affected by a given probability of failure.

Specifically, we indicate with $P_E(\bar{t},t_R)$ the memory loss probability, i.e. the probability to find the wrong value of the bit when the memory is interrogated during the entire time $\bar{t}$, since its first writing. In any practical application it is interesting to set the acceptable probability P_E and the desired memory duration time $\bar{t}$, then to deduce what is the required t_R to be used for the refreshing period that satisfy those conditions. By the moment that the refresh operation has an energetic cost Q, we are interested in establishing a relation between Q and t_R.

Based on these considerations we are now in position to state the purpose of our work in the following terms: what are fundamental energy limits associated with the goal of preserving a given bit for a time $\bar{t}$, with a probability of failure not larger than P_E, by executing the refresh procedure with periodicity not longer than t_R ?

Results

In order to find the energetic cost of remembering, we use a physical model that describes the dynamics of the memory in terms of a relevant variable $x(t)$, a stochastic force $\xi(t)$ (e.g. thermal noise for ICT nanoscale devices), a dissipative processes $\gamma(t)$ and the confining potential $V(x)$ (in fig. 1a). Due to $\xi(t)$, the system dynamics can be

analysed in terms of a proper Fokker-Planck equation [10], that gives the time evolution of the probability density $p(x,t)$ to find the system in $(x, x+dx)$ at time t.

Let us assume we want to preserve over time a memory where the bit 1 is stored. Thus the initial state of the memory is the 1 symbol. This means that $p_i=p(x,0)$ (fig. 1b) is a sharp peak centred in x>0. If we leave the memory alone, $p(x,t)$ will first relax inside the right well and then it will diffuse into the left well of the potential, by growing a probability $P_0(t,p_i) = \int_{-\infty}^{0} p(x,t)dx$ (fig. 1b to fig. 1f). P_0 increases with time and eventually it will reach its equilibrium condition where the memory is definitely lost (fig. 1f). To fight this phenomenon, we perform at time t_R a refresh operation that takes a time $t_p \ll t_R$. Let's suppose that after a time t_R the system is still in the "1" (right) well. This refresh operation reshapes the peaks of the probability density function into the initial $p_i=p(x,0)$ (see supplementary information): the memory is thus preserved and the cycle starts again. We have assumed that the refresh operation finds the system still in the right well. Clearly, as the time passes, the probability of finding the system in the wrong well increases and so increases the probability of error P_E. At time t_R, before the first refresh occurs, we have $P_E = P_0(t_R,p_i)$, thus the probability of still being in the right well is $1- P_0(t_R,p_i)$. If we repeat this procedure $N= \bar{t}\,/t_R$ times, this probability would be $(1- P_0(t_R,p_i))^N$ and thus the probability of error will be:

$$P_E(\bar{t}, t_R, p_i) = 1 - (1 - P_0(t_R, p_i))^{\frac{\bar{t}}{t_R}} \qquad (1)$$

As we have introduced above, our aim is to find the minimum energy associated with the goal of preserving the memory for a time $\bar{t}$ with a probability of error smaller than P_E while performing the refresh operation with periodicity t_R. From (1) we obtain a value $t_R=t_R(t,P_E,p_i)$ that provides the maximum refreshing interval that satisfies the given conditions. In fig. 2 we present t_R as obtained from the numerical solution of relevant Fokker-Plank equation (see supplementary information). Clearly, the larger $\bar{t}$ and the smaller P_E, the shorter is t_R, as expected.

In order to address the existence of any fundamental energy limit associated with the goal of preserving the given bit we need to establish a connection between these relevant quantities and the energy required to operate the refresh operation. Based on what we said before, the refresh operation consists in transforming $p(x,t_R)$ into $p_i=p(x,0)$ inside the single well that encodes the bit. We also assume that $t_R << \tau_K$ holds, so we can approximate the dynamics in each well with that of a harmonic oscillator near a potential minima x_m. With these approximations, we can locally approximate the real $p(x,t)$ with a Gaussian peak centred around x_m that has a total area equal to the probability of the system to be in that well and a standard deviation $\sigma(t)$ that changes as the refresh takes place[11]. From this perspective the refresh operation consists in applying an external force whose effect is to change $\sigma_f = \sigma(t_R)$ into $\sigma_i = \sigma(0)$. The latter is a design parameter, while the former depends on the intrawell relaxation mechanisms and, in the harmonic approximation, it is given by

$$\sigma(t_R)=\sqrt{\sigma_w^2 + e^{-\frac{t_R}{\tau_w}}(\sigma_i^2 - \sigma_w^2)} \qquad (2)$$

where σ_w and τ_w indicate the equilibrium standard deviation and the relaxation time, in the harmonic potential, respectively (see supplementary information).

What is the minimum energy required to operate this refreshing procedure? In order to answer this question we perform an experiment where the relevant observable $x(t)$ is represented by the position of the tip of a micro cantilever subjected to thermal noise and a potential $V(x)$ defined by an elastic restoring force of the mechanical structure and a repulsive electromagnetic potential determined by the voltage on the electromagnetic coil (fig. 3a) (for details on the experimental setup please see Methods). In the regime of small oscillations the dynamics of $x(t)$ can be approximated to that of a harmonic oscillator with $V(x) \cong V_H(x)$. Here the stochastic force is represented by the thermal noise affecting the micro cantilever and the dissipative forces are modelled according to the Zener Theory as a combination of viscous, thermo elastic and clamping effects[8] (see Methods). In order to mimic the refresh operation in our system, we apply an electromagnetic force that modifies the

effective potential $V_H(x)$ (fig. 3b) as follows: at time $t=t_R$ the electrostatic potential is linearly changed from $V=0.5V$ to $V=0V$. During this operation the effective potential $V_H(x)$ changes its configuration from the red curve to the blue curve (fig. 3b). The probability density function of the tip position changes accordingly (fig. 3c). The entire procedure takes a time t_p. After this time, the voltage on the coil is suddenly changed back to $V=0.5V$ and kept in this condition for a time t_R.

In fig. 4a we show the energy required to operate a single refresh operation as a function of the protocol time t_p. Details on how the energy is measured are discussed in Methods. When t_p increases, the energy required to operate the refresh operation approaches a lower bound that can be identified with the fundamental limit $Q_m = -T\Delta S$, where $\Delta S=S(0)-S(t_R)$ is the system entropy variation during the refresh operation. By the moment that the refresh requires a decrease in the system entropy, the energy has to be provided in terms of work done on the system. This minimum amount of energy required by the entropy variation is clearly a function of the spread of the probability density $p(x,t)$ occurring during the time t_R. If we model the system entropy according to Gibbs with $S(t) = -\int_{-\infty}^{+\infty} p(x,t)\,\ln\big(p(x,t)\big)dx$, we can express ΔS in terms of the ratio σ_f/σ_i (see supplementary information for details), during the refresh operation, as

$$\Delta S = k_B\, ln\left(\frac{\sigma_f}{\sigma_i}\right) \tag{3}$$

In fig. 4b we show the theoretical minimum energy required for the refresh operation as a function of $ln(\sigma_f/\sigma_i)$.

We are now in position to answer the question that originated this work: it does indeed exists a fundamental energy limit that links the goal of preserving the digital memory, in order that after a time $\bar{t}$ the failure probability is less than P_E. This limit can be expressed according to (2) and (3) as:

$$Q = -N\,T\Delta S = \frac{\bar{t}}{t_R} k_B T\, ln\left(\frac{\sqrt{\sigma_w^2 + e^{-\frac{t_R}{\tau_w}(\sigma_i^2 - \sigma_w^2)}}}{\sigma_i}\right) \quad (4)$$

Operatively, once we pick the two required preserving conditions, $\bar{t}$ (memory duration) and P_E (probability of memory loss), we can compute $t_R(\sigma_i)$ from (1) and thus $Q(\sigma_i)$ from (4) (see fig. 5a) or, alternatively, we can compute $\sigma_i(t_R)$ from (1) and $Q(t_R)$ from (4) (see fig. 5b).

In fig. 5a we show the minimum energy $Q(t_R)$ for a given choice of P_E and $\bar{t}$. It is interesting to observe that this is an increasing function of t_R that shows two relevant features: (ia) it approaches the value 0 when t_R goes to 0 and (iia) it grows to infinity when t_R approaches a finite value t_{RMax}. The feature (ia) indicates that it is indeed possible to preserve the memory for a time $\bar{t}$ with probability P_E by spending zero energy. Clearly this is possible as t_R approaches 0. Such a condition, although not forbidden by the law of physics, raises some practical issues as it implies a continuous refreshing process with no memory availability for use. The divergence in (iia) can be understood as a consequence of (1). As a matter of fact when we set our desired P_E, that is the probability of memory loss after the time $\bar{t} > t_R$, this cannot be smaller than P_0 that is the probability of memory loss at t_R. As a consequence it does exist a maximum refresh time t_{RMax} above which we cannot satisfy the required condition anymore.

In fig. 5b we show the minimum energy $Q(\sigma_i)$ for a given choice of P_E and $\bar{t}$. This is a decreasing function of σ_i that shows two relevant features: (ib) it reaches the value 0 when σ_i goes to σ_w and (iib) it grows to infinity when σ_i approaches 0. Condition (ib) indicates, as stated above, that it is possible to preserve the memory for a time $\bar{t}$ with probability P_E by spending zero energy and this is realized when σ_i approaches σ_w. On the other end, condition (iib) implies that the amount of energy required to keep the memory grows boundless when we select an arbitrarily small confinement for the initial probability density ($\sigma_i \simeq 0$). This last condition, in any real physical system, is

limited by the Heisenberg indetermination principle that sets a lower bound[12] for the initial standard deviation of p_i, i.e. $\sigma_i \geq \sigma_{iMin}$ (see supplementary information). As a consequence the amount of energy required in fig. 5b reaches a finite maximum. We point out that the existence of a finite σ_{iMin} has another important consequence: it sets a limit on our capability to preserve a given memory forever, no matter what energy we spend or how often we refresh. This is apparent when we use (1) to explicitly write $\bar{t} = t_R \, ln(1-P_E)/ln(1-P_0)$. Once we set P_E and select a finite t_R, we can make $\bar{t}$ as large as we want by properly selecting P_0 small enough. However, the existence of $\sigma_{iMin}>0$ sets a limit on how small we can make P_0. Specifically it exist a $P_{0Min} = P_0(t_R, p_i(\sigma_{iMin}))$ and thus a $\bar{t}_{\mathrm{Max}} = t_R \, ln(1-P_E)/ln(1-P_{0Min})$. In practical memories this time limit $\bar{t}_{\mathrm{Max}}$ can be very large. As an example we consider a micromechanical memory device[13]. If we assume the distance between the two wells $x_m = 1\ 10^{-9}$ m and a refresh period $t_R = 6.6\ 10^{-3}$ s, we have $\sigma_{iMin} = 9.6\ 10^{-20}$ m. If we set $P_E = 1\ 10^{-6}$ we have $\bar{t}_{\mathrm{Max}} = 5.9\ 10^{7}$ s (approximately 2 years). On the other hand, if we set $P_E = 1\ 10^{-4}$ we have $\bar{t}_{\mathrm{Max}} = 5.9\ 10^{9}$ s (approximately 200 years).

Until now we have considered the idealized case in which the protocol time t_p can be made arbitrarily small compared to the refresh time t_R. In most practical cases, however, in order to approach the adiabatic condition, and thus the minimum energy consumption, we need to take into account a finite t_p. This is well apparent in the inset of fig. 5a, where we show the dissipated energy Q as a function of the protocol time t_p for a given choice of P_E, $\bar{t}$ and t_R. Those are computed by following the procedure in [14] with the aid of [15] to obtain the desired final σ_i. The effect of non-negligible protocol time t_p is twofold: ic) it sets a lower limit to the refresh time $t_R > t_p$. iic) It adds an energy burden to the minimum energy Q_m.

Conclusions

In conclusion we have shown that in order to preserve a memory for a given time with a given error probability, it is possible indeed to spend an arbitrarily little amount of energy, provided that the refresh procedure is performed arbitrarily often (fig. 5a) or arbitrarily close to thermal equilibrium (fig. 5b).

We have also shown that the Heisemberg indetermination principle, that prescribes a maximum possible confinement of the relevant observable, implies the existence of a finite minimum uncertainty during the writing operation. This uncertainty reflects in the existence of a minimum width for the initial probability density of the memory device. The most dramatic consequence of this minimum width is that refresh strategies will inevitably fail after a maximum time given by the fundamental laws of physics. In other terms: no matter how much energy we invest, how often we refresh or how close to equilibrium we operate, there is a finite time after which any memory will be irremediably lost.

Methods

Experimental setup details. All measurements are carried on in a vacuum chamber at $P = 10^{-4}$ mbar and at room temperature ($T = 300$ K). The mechanical structure is a 200 μm long V-shaped cantilever providing a nominal stiffness, $k = 0.08$ N m^{-1}, and a resonance frequency of 17 kHz. A fragment of NdFeB (neodymium) magnet is attached to the cantilever tip with bi-component epoxy resin. To set the magnetization to a known direction the system is heated up to 670 K, above its Curie temperature in the presence of a strong external magnetic field with the desired orientation. With this additional mass the resonance frequency decreases to 5.3 kHz. The quality factor of the system is $Qf = 300$, resulting in a relaxation time $t_{Relax} =$ 20 ms. The deflection of the cantilever, x, is measured by an AFM-like optical lever: the deflection of the laser beam (1064 nm) due to the bend of the cantilever is detected by a two quadrants photo detector. The response of the photo detector in the linear regime is $x = r_{\mathrm{x}}\Delta V_{\mathrm{PD}}$ with $r_{\mathrm{x}} = 1.5375 \cdot 10^{-7}$ m V^{-1}. Position and voltage measurements were digitalized at 50 kHz. To modify the potential of the system a repulsive electromagnetic potential is introduced by means of an electromagnetic coil facing the magnet of the cantilever tip. By varying the voltage on the coil, and thus the current, a repulsive magnetic field is generated and a flattening on the potential is then achieved.

Heat production evaluation. Considering no variation on the internal energy of the system ($\Delta V=0$) the heat produced, Q, corresponds to the work done on the system, W. For a given trajectory $x(t)$, W is given by the integral:

$$W = \int_0^{t_p} \frac{\partial V(x,\lambda)}{\partial \lambda} \frac{\partial \lambda}{\partial t} dt$$

where t_p is the protocol time duration, $V(x,\lambda)$ is the total potential energy of the system and λ is the control parameter, i.e. the voltage applied to the electromagnetic coil.

Dissipative model based on Zener theory. The dissipative model for the data in fig. 4a is based on the Zener theory, assuming the dissipative dynamics expressed as the result of frictional forces that represent the imaginary component of a complex elastic force $-k(1+i\phi)$ [16] where the loss angle ϕ is a function of the frequency expressed as: $\phi(\nu) = \phi_{\text{th-el}} + \phi_{\text{vis}} + \phi_{\text{clamp}}$. Here $\phi_{\text{th-el}}$ and ϕ_{vis} are the thermo-elastic [17, 18] and viscous damping that can be assumed to be proportional to the frequency for frequencies much smaller than the cantilever characteristic frequency, and ϕ_{clamp} represents the clamp recoil losses ($\phi(\nu) \propto \nu^3$) [19].

Data availability statement

The data that support the findings of this study are available from the corresponding authors upon request.

References

[1] Landauer, R. Irreversibility and heat generation in the computing process, IBM J. Res. Dev., 5, 183–191, (1961)

[2] Mancini, S., Pierini, R. and Wilde, M. M. Preserving information from the beginning to the end of time in a Robertson–Walker spacetime. New Journal of Physics 16 (2014) 123049 doi:10.1088/1367-2630/16/12/123049.

[3] Burak Y., Fiete I.R., Fundamental limits on persistent activity in networks of noisy neurons. Proc Natl Acad Sci U S A. 2012 Oct 23;109(43):17645-50. doi: 10.1073/pnas.1117386109.

[4] M. Cristina Diamantini and Carlo A. Trugenberger, Generalized Landauer Bound as Universal Thermodynamic Entropy in Continuous Phase Transitions, Phys RevE. 89 (2014) 052138

[5] Markov, I. L. Limits on fundamental limits to computation. Nature 512, 147–154 (14 August 2014) doi:10.1038/nature13570.

[6] Berut, A., Arakelyan, A., Petrosyan, A., Ciliberto, S., Dillenschneider, R., Lutz, E. Experimental verification of Landauer/'s principle linking information and thermodynamics, Nature 483 (7388), 187-189

[7] Chiuchiú D., Diamantini, M. C. and Gammaitoni, L. Conditional entropy and Landauer principle, *EPL* **111** 40004 (2015)

[8] López-Suárez, M., Neri, I. and Gammaitoni, L. Sub-kBT micro-electromechanical irreversible logic gate. *Nature Communications* **7**, Article number: 12068. (2016). doi:10.1038/ncomms12068

[9] Bruce, J., Ng D. and Wang D. Memory Systems: Cache, DRAM, Disk. Morgan Kaufmann ISBN 0123797519 (2007).

[10] Risken, H. The Fokker–Planck Equation: Methods of Solutions and Applications. 2nd edition, Springer Series in Synergetics, Springer, 1996.

[11] Chiuchiú, D. Time-dependent study of bit reset. *EPL* **109** 30002 (2015)

[12] Diamantini, M. C., Gammaitoni, L., and Trugenberger, C. A. Landauer Bound for Analog Computing Systems. Phys. Rev. E94, 012139 (2016). DOI: 10.1103/PhysRevE.94.012139

[13] Neri, I. and López-Suárez M. Heat production and error probability relation in Landauer reset at effective temperature. *Scientific Reports* **6**, Article number: 34039 (2016) doi:10.1038/srep34039

[14] Van den Broeck, C. and Esposito, M. Three faces of the second law. II. Fokker-Planck formulation, Phys. Rev. E, 82 (1), 011144 (2010)

[15] Martinez, I. A., Petrosyan, A., Guery-Odelin, D., Trizac, E., Ciliberto, S. Engineered swift equilibration of a Brownian particle, Nat Phys 12 (9) 843-846 (2016)

[16] Zener, C. in Elasticity and anelasticity of metals (University of Chicago press, 1948).

[17] Zener, C. Internal friction in solids I. Theory of internal friction in reeds. Phys. Rev. 52, 230 (1937).

[18] Zener, C. Internal friction in solids II. General theory of thermoelastic internal friction. Phys. Rev. 53, 90 (1938).

[19] Saulson, P. R. Thermal noise in mechanical experiments. Phys. Rev. D 42, 2437 (1990).

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Author Contributions

D.C. provided the dynamical model and performed the digital simulation.
M.L.S. and I.N. designed the experiment and performed the measurements.
M.C.D. provided the model for the maximum confinement.
L.G. supervised the work and provided the dissipative model.
All authors contributed to the data analysis and to the writing of the manuscript.

Competing Financial Interest statement

The authors declare no competing financial interests.

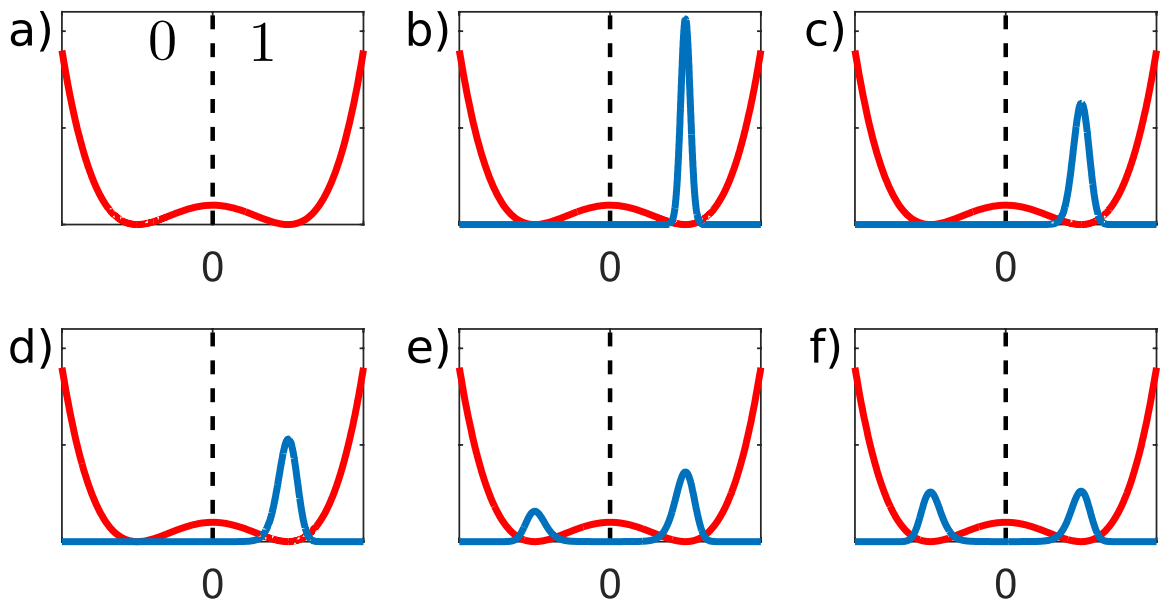

Figure 1 – A generic binary memory is represented here in terms of the stochastic dynamics of a variable *x(t)* subjected to the bistable potential *V(x)* (a). Here a potential barrier separates the two logic states. (b) a bit with logic value 1 is stored in this memory. According to the relaxation to equilibrium process, *p(x,t)* (blue curves) will first relax inside the right well (c) and (d) and then it will diffuse into the left well of the potential (e) to eventually reach global equilibrium (f). In this condition the memory of the stored bit is definitely lost.

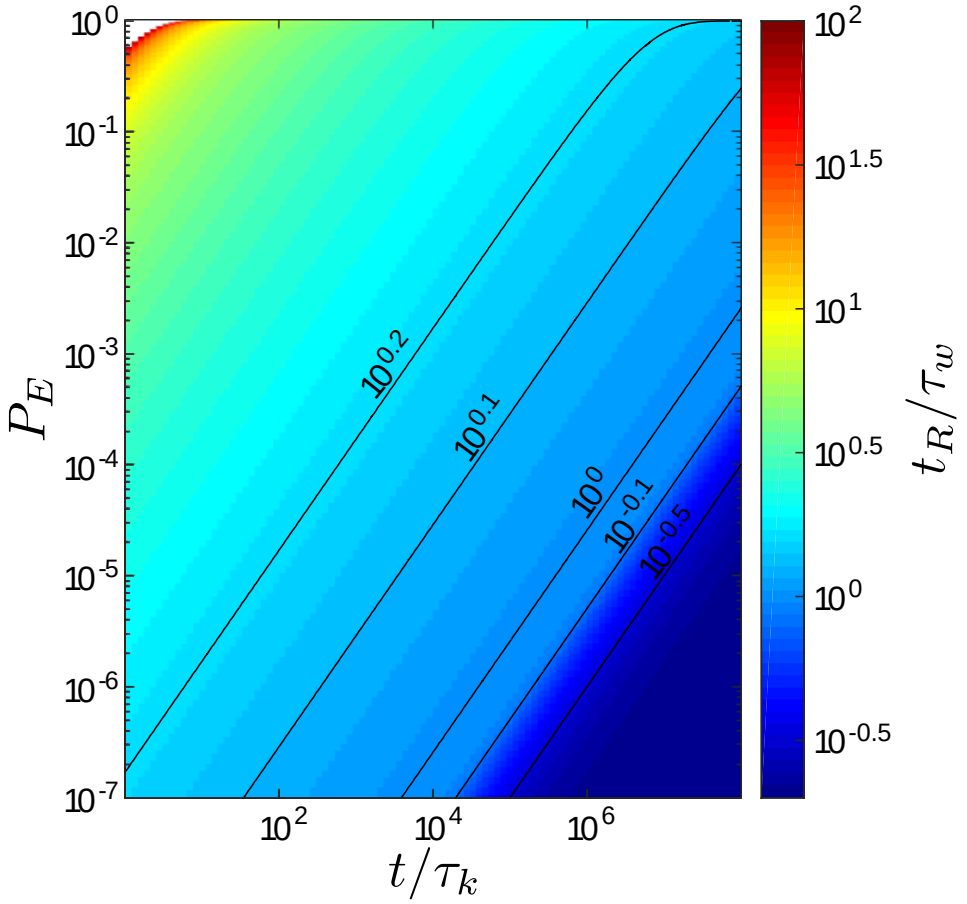

Figure 2: t_R as function of $\bar{t}$ and P_E for a memory represented by an overdamped system in a bistable Duffing potentials. Here $\bar{t}$ is given in unit of the global thermalization time τ_k, while t_R is given as a multiple of τ_w, i.e. relaxation time within one well of the potential. The results here presented are obtained with $\tau_k = 5.3 \cdot 10^4\ \tau_w$ (see supplementary information for detail).

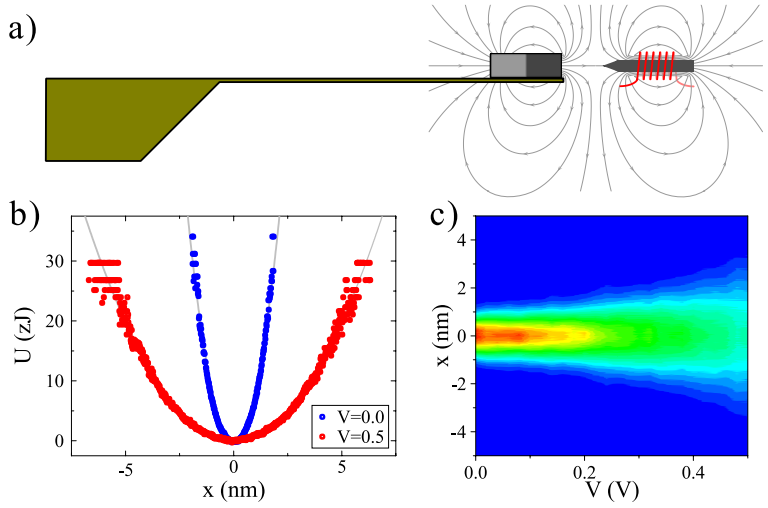

Figure 3 - Experimental setup. (a) Lateral view. A magnet on the cantilever tip and an electromagnetic coil are used to change the effective stiffness of the cantilever. (b) Potential energy of the cantilever tip, for two different voltages at the coil, reconstructed from the probability density function. Solid gray lines represent the fitted harmonic potential. (c) Probability density of the cantilever tip position $p(x)$ as a function of the voltage applied at the coil. The greater is the voltage, the greater is the repulsive force, resulting in a flattening of the potential and in an increasingly spread probability density (higher to lower from red to blue).

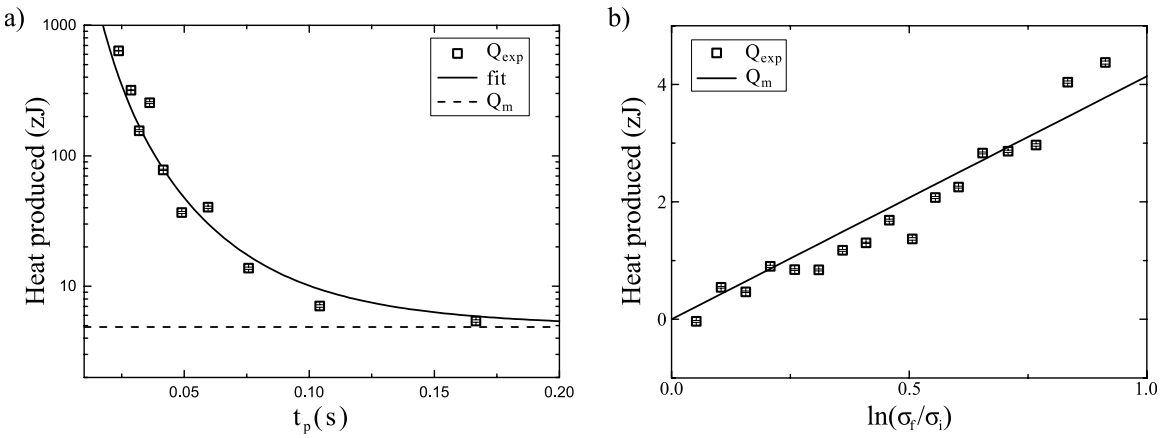

Figure 4 – Experimental results of produced heat. (a) Produced heat during the operation of a single refresh as function of protocol time t_p. Increasing t_p the procedure approaches the adiabatic condition and the produced heat tends to the lower bound identified with the fundamental limit Q_m=-$T\Delta S$. The dots represent the estimated heat from the experiment, while the solid line is the fit with the dissipative model (see Methods). (b) Produced heat during a single refresh operation for different variation of entropy. The solid dots represent the estimated heat from experiments while the solid line represents the theoretical model in (3).

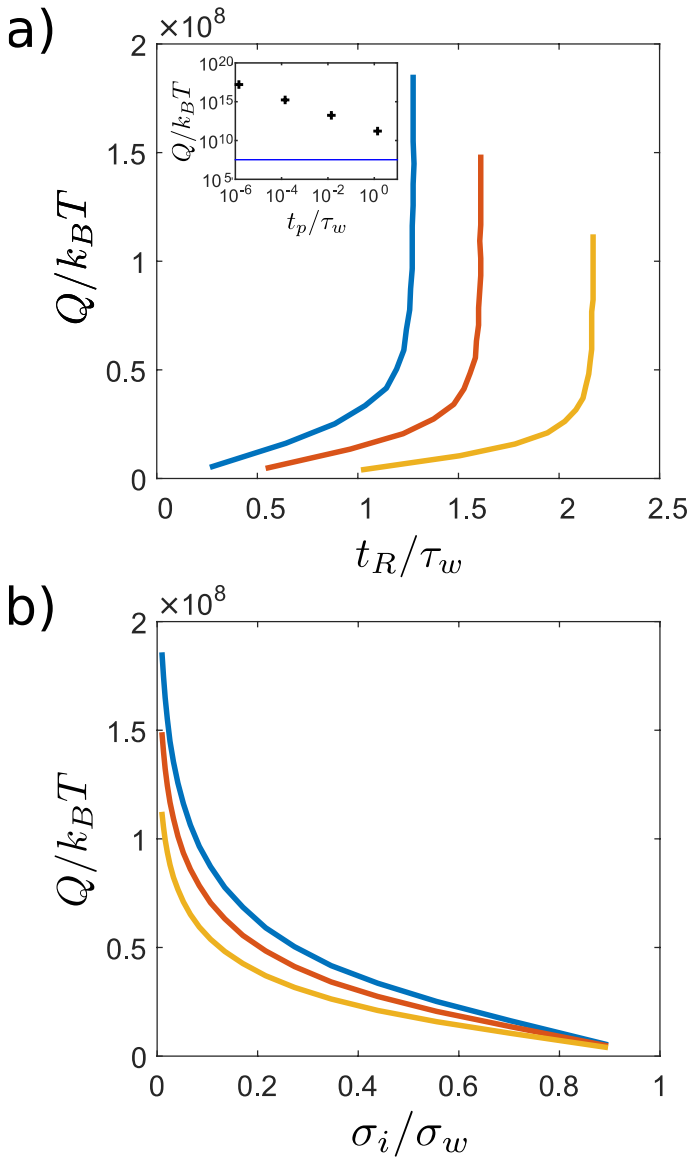

Figure 5: plots of the heat Q required to preserve the memory for $\bar{t} = 10^3\tau_k$ as a function of t_R (a) and σ_i (b). In both plots blue lines are obtained with P_E=10^{-6}, Red lines with P_E=10^{-4}, yellow lines with P_E=10^{-2}. Inset in panel (a) shows experimental values for Q *vs* t_p/τ_w, when $\bar{t} = 10^3\tau_k$, P_E=10^{-6} and t_R=τ_w. The blue line marks the adiabatic value Q=Q_m in (5).

Supplementary methods

Computation of Figure 2

We consider a memory system represented by an overdamped colloidal particle in a viscous fluid with a bistable Duffing potential. Its dynamics can be described with a Fokker-Plank equation

$$\frac{\partial p}{\partial t} = \frac{\partial}{\partial x}\left(\frac{\partial V}{\partial x}p\right) + \frac{k_B T}{\Delta U}\frac{\partial^2 p}{\partial x^2}, \tag{SM.1}$$

with

$$V(x) = 4\left(-\frac{x^2}{2} + \frac{x^4}{4}\right) \tag{SM.2}$$

where k_B is the Boltzmann constant, T is the temperature of the fluid and ΔU is the height of the barrier separating the two minima of the potential.

To compute fig. 2, we take

$$p(x,0) = \frac{\exp\left(-\frac{(x-1)^2}{2\sigma_i^2}\right)}{\sqrt{2\pi}\sigma_i} \tag{SM.3}$$

as initial condition for (SM.1). In particular, σ_i is such that $p(x,t)$ broadens inside the right well of $V(x)$ before developing a clean-cut second peak in the left well of the potential. We then solve eq.(SM.1) with the Matlab `pdepe` function. With the solution we compute

$$P_0(t_R) = \int_{-\infty}^{\infty} p(x, t_R) \tag{SM.4}$$

for different refresh times t_R, and then we evaluate the failure probability

$$P_E(t, t_R) = 1 - (1 - P_0(t_R))^{\frac{t}{t_R}} \tag{SM.5}$$

for different values of t_R and $t \gg t_R$. As a last step, we use a spline fit of $P_E(t, t_R)$ to sample $t_R(P_E, t)$ for different values of P_E and t. The results obtained in this way are plotted in fig. 2.

Derivation of (2) and (3)

We derive here two important equations given in the main text, namely (2) and (3). To derive (2) we assume that $\Delta U \gg k_B T$. This implies that the intra-well relaxation mechanisms of the system are faster than the inter-well ones. If we are interested in intra-well dynamics only, then a satisfactory form for the $p(x,t)$

is

$$p(x,t) = p_0(x,t) + p_1(x,t) \tag{SM.6a}$$

$$p_0(x,t) = P_0 \frac{\exp\left(-\frac{(x+1)^2}{2\sigma(t)^2}\right)}{\sqrt{2\pi}\sigma(t)} \tag{SM.6b}$$

$$p_0(x,t) = (1-P_0) \frac{\exp\left(-\frac{(x-1)^2}{2\sigma(t)^2}\right)}{\sqrt{2\pi}\sigma(t)} \tag{SM.6c}$$

$$\tag{SM.6d}$$

where P_0 is constant. We substitute (SM.6) in (SM.1) and then we approximate (SM.2) with an harmonic potential by taylor-expanding around $x = \pm x_m$. This yields two distinct equations

$$\frac{\partial p_0}{\partial t} - 8\left(p_0 + (x+1)\frac{\partial p_0}{\partial x}\right) - \frac{k_B T}{\Delta U}\frac{\partial^2 p_0}{\partial x^2} = 0 \tag{SM.7a}$$

$$\frac{\partial p_1}{\partial t} - 8\left(p_1 + (x-1)\frac{\partial p_1}{\partial x}\right) - \frac{k_B T}{\Delta U}\frac{\partial^2 p_1}{\partial x^2} = 0 \tag{SM.7b}$$

$$\tag{SM.7c}$$

where used the fact that $p_1(x,t)$ ($p_0(x,t)$) does not affect the dynamics of the system in the left (right) well of $V(x)$ if $\Delta U \gg k_B T$. Eq.(SM.7) can be combined into

$$\begin{aligned}\int_{-\infty}^{\infty} &\left(\frac{\partial p_0}{\partial t} - 8\left(p_0 + (x+1)\frac{\partial p_0}{\partial x}\right) - \frac{k_B T}{\Delta U}\frac{\partial^2 p_0}{\partial x^2}\right)(x+1)^2 \mathrm{d}x \\ + \int_{-\infty}^{\infty} &\left(\frac{\partial p_1}{\partial t} - 8\left(p_1 + (x-1)\frac{\partial p_1}{\partial x}\right) - \frac{k_B T}{\Delta U}\frac{\partial^2 p_1}{\partial x^2}\right)(x-1)^2 \mathrm{d}x = 0,\end{aligned} \tag{SM.8}$$

which reduces to

$$\frac{\partial \sigma(t)^2}{\partial t} + 16\sigma(t)^2 - 2\frac{k_B T}{\Delta U} = 0. \tag{SM.9}$$

(SM.9) describes the time evolution of $\sigma(t)$ when intra-well relaxation mechanisms occurs. Its analytic solution for an initial condition $\sigma(0) = \sigma_i$ is

$$\sigma(t) = \sqrt{\frac{k_B T}{8\Delta U} + \exp\left(-16t\right)\left(\sigma_i^2 - \frac{k_B T}{8\Delta U}\right)} \tag{SM.10}$$

which is the dimensionless version of the eq.(2) given in the main text.

To compute (3) we assume that the refresh protocol preserves the symmetry of $V(x)$ so that $p(x,t)$ can be written as (SM.6) during the whole refresh procedure. As a consequence, the sole effect of a refresh operation with duration τ_p is to transform

$$p(x,t) = P_0(t)\frac{\exp\left(-\frac{(x+1)^2}{2\sigma(t)^2}\right)}{\sqrt{2\pi}\sigma(t)} + (1-P_0(t))\frac{\exp\left(-\frac{(x-1)^2}{2\sigma(t)^2}\right)}{\sqrt{2\pi}\sigma(t)} \tag{SM.11}$$

into

$$p(x,t+\tau_p) = P_0(t)\frac{\exp\left(-\frac{(x+1)^2}{2\sigma_i^2}\right)}{\sqrt{2\pi}\sigma_i} + (1-P_0(t))\frac{\exp\left(-\frac{(x-1)^2}{2\sigma_i^2}\right)}{\sqrt{2\pi}\sigma_i} \tag{SM.12}$$

where $\sigma(t)$ is given by eq.(SM.10), $P_0(t)$ is fitted from the numerical solution of (SM.1) with (SM.2), and $\sigma_i = \sigma(0)$. Given

$$S(t) = -k_B \int_{-\infty}^{\infty} p(x,t)\ln p(x,t)\mathrm{d}x \tag{SM.13}$$

we compute the entropy variation $\Delta S = S(t+\tau_p) - S(t)$ of the refresh protocol. Because of the $\Delta U \gg k_B T$ assumption, we have that

$$\Delta S \approx -k_B \left(\int_{\infty}^{\infty} \frac{\mathrm{e}^{-\frac{x^2}{2\sigma_i^2}}}{\sqrt{2\pi}\sigma_i} \ln\left(\frac{\mathrm{e}^{-\frac{x^2}{2\sigma_i^2}}}{\sqrt{2\pi}\sigma_i}\right)\mathrm{d}x - \int_{\infty}^{\infty} \frac{\mathrm{e}^{-\frac{x^2}{2\sigma(t)^2}}}{\sqrt{2\pi}\sigma(t)} \ln\left(\frac{\mathrm{e}^{-\frac{x^2}{2\sigma(t)^2}}}{\sqrt{2\pi}\sigma(t)}\right)\mathrm{d}x \right), \tag{SM.14}$$

which reduces to

$$\Delta S \approx -k_B \ln\left(\frac{\sigma(t)}{\sigma_i}\right). \tag{SM.15}$$

By using (SM.15) with $t = t_R$ we obtain (3).

Minimum value for σ_i

We discuss here the existence of the minimum possible value for σ_i. First of all, we observe that $\sigma_i \to 0$ is a singular limit in eq.(SM.15). This is inconsistent with the third law of thermodynamics, so there must be a minimum value for σ_i. This is given by the Heisemberg indetermination principle. In the best case scenario this reads

$$\sigma_x \sigma_p = \frac{\hbar}{2}. \tag{SM.16}$$

where σ_x (σ_p) is the uncertainity on the position x (momentum p). According to the equipartition theorem,

$$\sigma_p = m\sqrt{\langle v^2\rangle - \langle v\rangle^2} = \sqrt{mk_BT}, \tag{SM.17}$$

so we have that

$$\sigma_x = \frac{\hbar}{2\sqrt{mk_BT}} \tag{SM.18}$$

Eq.(SM.18) sets the minimum possible uncertainty for σ_x. Since σ_i describes the uncertainty of the initial x value, we therefore have that $\sigma_i \geq \sigma_{iMin} = \frac{\hbar}{2\sqrt{mk_BT}}$. The existence of a σ_{iMin} implies that, even at $t = 0$, the probability of error P_0 is greater than zero.